

No.2563C

2SK669

N-Channel Enhancement MOS Silicon FET

Very High-Speed Switch, Analog Switch Applications

Applications

· Analog switches, low-pass filters, very high-speed switches

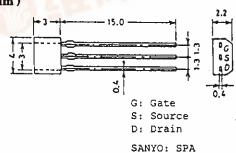
Features

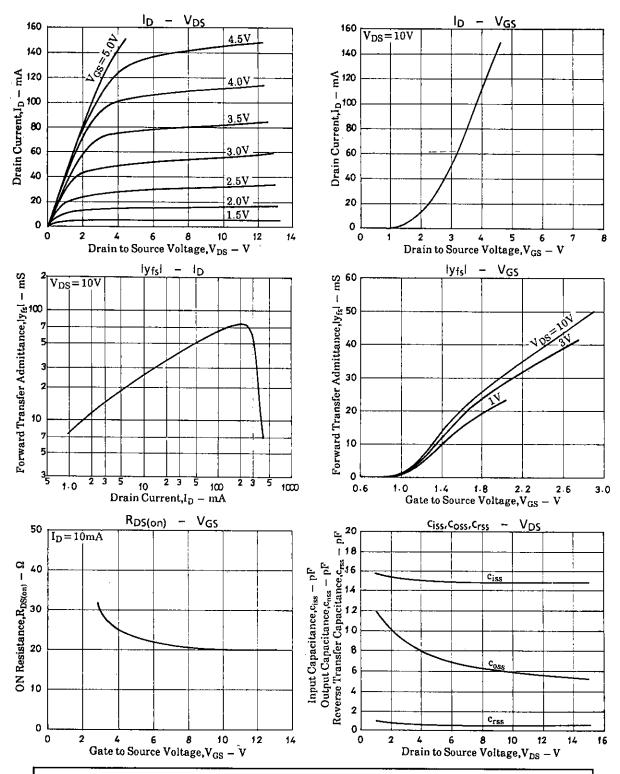
- · Large lyfsl
- · Enhancement type
- · Small ON resistance

Absolute Maximum Ratings at	$t Ta = 25^{\circ}C$		unit
Drain to Source Voltage	$ m V_{DS}$	50	V
Gate to Source Voltage	v_{GS}^{-3}	±12	V
Drain Current	$I_{\mathbf{D}}$	100	mΑ
Drain Current (Pulse)	I_{DP}	300	mA
Allowable Power Dissipation	$P_{\mathbf{D}}$	200	mW
Channel Temperature	Tch	125	$^{\circ}\mathrm{C}$
Storage Temperature	Tstg	-55 to + 125	°C

Electrical Characteristics at Ta = 25°C			min	typ	max	unit
Drain to Source	$V_{(BR)DS}$	$I_D = 10 \mu A, V_{GS} = 0$	50			V
Breakdown Voltage						
Gate Cutoff Current	I_{GSS}	$V_{GS} = 10V, V_{DS} = 0$		0.01	10	nΑ
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 100 \mu A$	0.3	0.9	1.5	V
Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1.0	μΑ
Forward Transfer Admittance	$ y_{fs} $	$V_{DS} = 10V, I_D = 50mA, f = 1kHz$	25	40		mS
Input Capacitance	c_{iss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		15		pF
Output Capacitance	coss	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		6		рF
Reverse Transfer Capacitance	c _{rss}	$V_{DS} = 10V, V_{GS} = 0, f = 1MHz$		0.5		pF
ON Resistance	R _{DS(on)}	$V_{DS} = 10V, I_D = 10mA$		20		Ω

Package Dimensions 2040 (unit: mm)





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